

# **Dual P-Channel 20 V (D-S) MOSFET**

PRODUCT SUMMARY						
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)			
- 20	0.155 at V <sub>GS</sub> = - 4.5V	- 1.8	2.7 nC			
	0.235 at V <sub>GS</sub> = - 2.5 V	- 1.5	2.7 110			

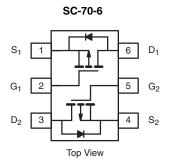
#### **FEATURES**

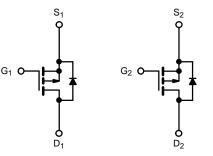
 Halogen-free According to IEC 61249-2-21 Definition



RoHS

- TrenchFET® Power MOSFET
- 100 % R<sub>g</sub> Tested
- Compliant to RoHS Directive 2002/95/EC





P-Channel MOSFET

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<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>A</sub> = 25 °C, unless otherwise noted)					
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	- 20	V	
Gate-Source Voltage		$V_{GS}$	± 12	v	
	T <sub>C</sub> = 25 °C		- 1.8		
Continuous Drain Current (T <sub>.I</sub> = 150 °C)	T <sub>C</sub> = 70 °C	I <sub>D</sub>	- 1.5		
Continuous Diam Current (1) = 130 C)	T <sub>A</sub> = 25 °C		- 1.6 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C		-1.1 <sup>b, c</sup>	A	
Pulsed Drain Current		I <sub>DM</sub>	- 2.5		
	T <sub>C</sub> = 25 °C		- 1.17		
Continuous Source-Drain Diode Current	T <sub>A</sub> = 25 °C	I <sub>S</sub>	- 0.95 <sup>b, c</sup>		
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	- P <sub>D</sub>	1.4		
	T <sub>C</sub> = 70 °C		0.9	W	
	T <sub>A</sub> = 25 °C		1.14 <sup>b, c</sup>	VV	
	T <sub>A</sub> = 70 °C		0.73 <sup>b, c</sup>		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>b, d</sup>	t ≤ 5 s	R <sub>thJA</sub>	93	110	°C/W	
Maximum Junction-to-Foot	Steady State	R <sub>thJF</sub>	75	90		

#### Notes:

- a.  $T_C = 25 \,^{\circ}C$ .
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 5 s
- d. Maximum under steady state conditions is 150 °C/W.



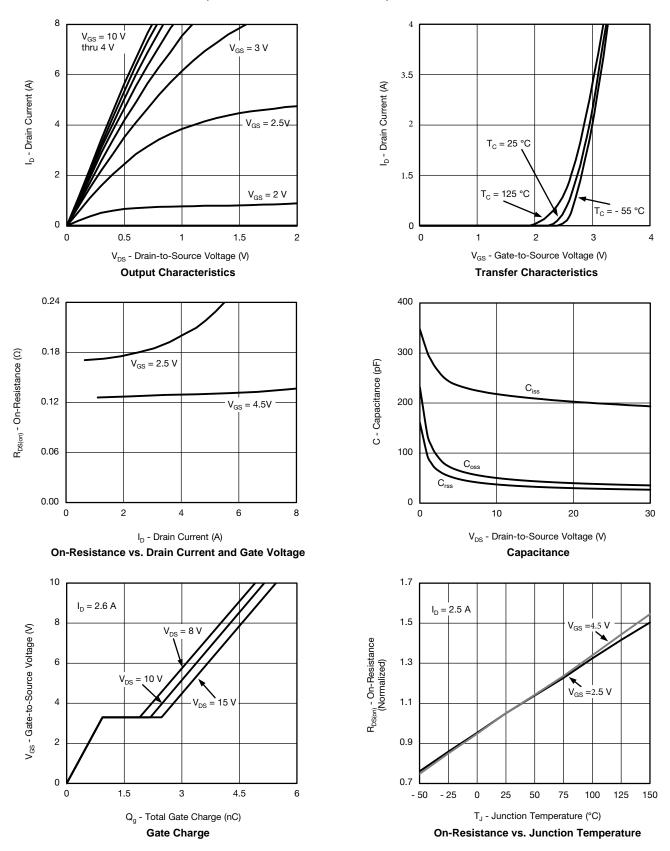
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static		<u> </u>			•	•	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = - 250 μA	- 20			V	
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I - 250 uA		- 17		mV/°C	
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_{J}$	I <sub>D</sub> = - 250 μA		3.5			
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = -250 \mu A$	- 0.5		- 1.5	V	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V			1		
		V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			10	μA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{V}$	- 8			Α	
	_	V <sub>GS</sub> = - 4.5V, I <sub>D</sub> = - 2.5 A		0.155		1	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 2.5 V, I <sub>D</sub> = - 1 A		0.235		Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 2.6 A		5		S	
Dynamic <sup>b</sup>					l		
Input Capacitance	C <sub>iss</sub>			210			
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = - 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz		45		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			33			
·	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}$	V <sub>DS</sub> = - 15 V, V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 2.6 A		5.2	8	nC	
Total Gate Charge				2.7	4		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -2.6 \text{ A}$		0.94			
Gate-Drain Charge	$Q_{gd}$			1.3			
Gate Resistance	R <sub>g</sub>	f = 1 MHz	2	7	14	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			39	59	ns	
Rise Time	t <sub>r</sub>	$V_{DD} = -15 \text{ V}, R_{L} = 7.1 \Omega$		25	38		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong$ - 2.1 A, $V_{GEN}$ = - 4.5 V, $R_g$ = 1 $\Omega$		13	20		
Fall Time	t <sub>f</sub>			9	18		
Turn-On Delay Time	t <sub>d(on)</sub>			5	10		
Rise Time	t <sub>r</sub>	$V_{DD} = -15 \text{ V}, R_{L} = 7.1 \Omega$		10	20		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong$ - 2.1 A, $V_{GEN}$ = - 4.5 V, $R_g$ = 1 $\Omega$		14	21		
Fall Time	t <sub>f</sub>			7	14		
<b>Drain-Source Body Diode Characteristi</b>	cs				I .	1	
Continuous Source-Drain Diode Current	I <sub>S</sub>	$T_C = 25  ^{\circ}C$		1.17		А	
Pulse Diode Forward Current	I <sub>SM</sub>			8			
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = - 2.1 A, V <sub>GS</sub> = 0 V		0.85	1.2	V	
Body Diode Reverse Recovery Time	t <sub>rr</sub>			13	20	ns	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	$Q_{rr}$ $I_F = -2.1 \text{ A, dI/dt} = 100 \text{ A/}\mu\text{s, T}_J = 25 °C$		6	12	nC	
Reverse Recovery Fall Time	_			9		ns	
Reverse Recovery Rise Time	t <sub>b</sub>			4			

#### Notes:

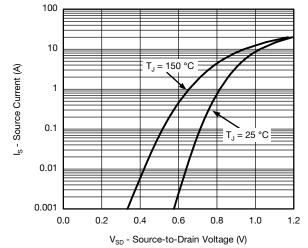
- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

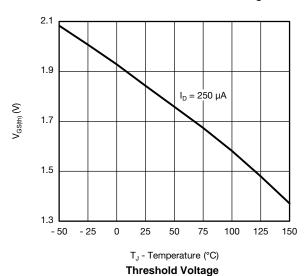






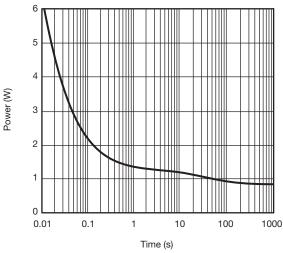


Source-Drain Diode Forward Voltage

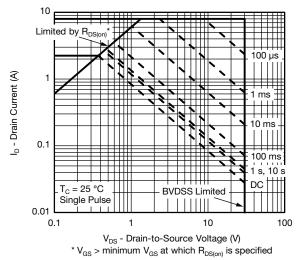


V<sub>GS</sub> - Gate-to-Source Voltage (V)

On-Resistance vs. Gate-to-Source Voltage

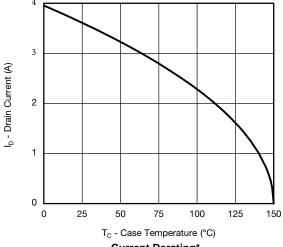


Single Pulse Power (Junction-to-Ambient)

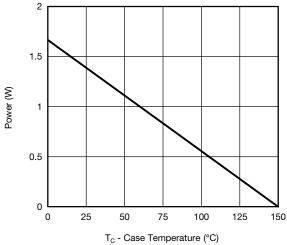


Safe Operating Area, Junction-to-Ambient

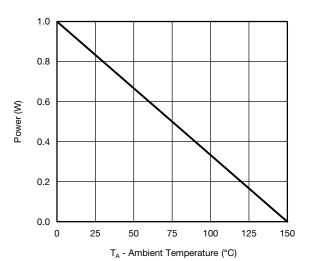




**Current Derating\*** 



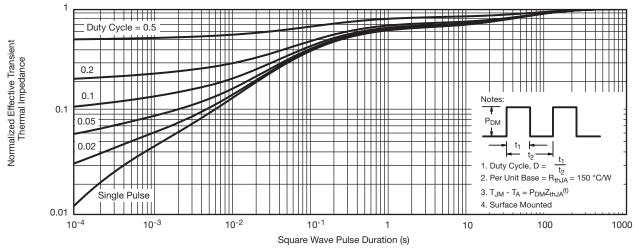




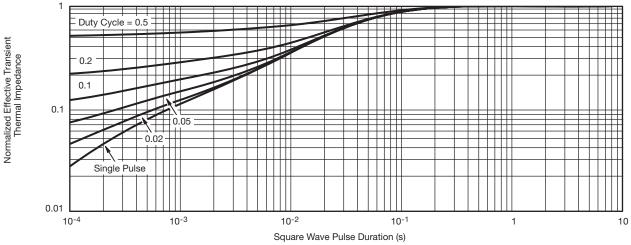
Power Derating, Junction-to-Ambient

<sup>\*</sup> The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot



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